

# PBSS4041PZ

# 60 V, 5.7 A PNP low V<sub>CEsat</sub> (BISS) transistor Rev. 01 — 31 March 2010

Product data sheet

#### 1. **Product profile**

#### 1.1 General description

PNP low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) medium power Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4041NZ.

#### 1.2 Features and benefits

- Very low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- High energy efficiency due to less heat generation
- AEC-Q101 qualified
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

#### 1.3 Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

#### 1.4 Quick reference data

Table 1. Quick reference data

| Symbol             | Parameter                               | Conditions   | Min          | Тур | Max        | Unit |
|--------------------|---|--|--------------|-----|------------|------|
| $V_{CEO}$          | collector-emitter voltage               | open base  | -            | -   | -60        | V    |
| I <sub>C</sub>     | collector current                       |  | -            | -   | -5.7       | Α    |
| I <sub>CM</sub>    | peak collector current                  | single pulse; $t_p \le 1 \text{ ms}$                 | -            | -   | <b>−15</b> | Α    |
| R <sub>CEsat</sub> | collector-emitter saturation resistance | $I_{C} = -5 \text{ A};$<br>$I_{B} = -500 \text{ mA}$ | <u>[1]</u> _ | 29  | 43.5       | mΩ   |

<sup>[1]</sup> Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 



# 2. Pinning information

Table 2. Pinning

| 10010 21 | 9           |                    |                |
|----------|-------------|--------------------|----------------|
| Pin      | Description | Simplified outline | Graphic symbol |
| 1        | base        |                    |                |
| 2        | collector   | 4                  | 2, 4           |
| 3        | emitter     |                    | 1 —            |
| 4        | collector   | 1 -1 -2 -3         | 3              |
|          |             |                    | sym028         |
|          |             |                    | Symozo         |

# 3. Ordering information

Table 3. Ordering information

| Type number | er Package |   |         |  |
|-------------|------------|---|---------|--|
|             | Name       | Description   | Version |  |
| PBSS4041PZ  | SC-73      | plastic surface-mounted package with increased heat sink; 4 leads | SOT223  |  |

# 4. Marking

Table 4. Marking codes

| 3           |              |
|-------------|--------------|
| Type number | Marking code |
| PBSS4041PZ  | PB4041PZ     |

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

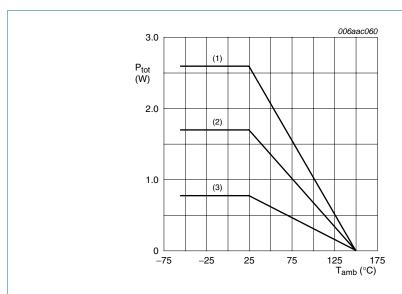
| Symbol          | Parameter                 | Conditions   | Min | Max         | Unit |
|-----------------|---------------------------|--|-----|-------------|------|
| $V_{CBO}$       | collector-base voltage    | open emitter   | -   | -60         | V    |
| $V_{CEO}$       | collector-emitter voltage | open base  | -   | -60         | V    |
| $V_{EBO}$       | emitter-base voltage      | open collector   | -   | <b>-</b> 5  | V    |
| I <sub>C</sub>  | collector current         |  | -   | <b>−5.7</b> | Α    |
| I <sub>CM</sub> | peak collector current    | $\begin{array}{l} \text{single pulse;} \\ t_p \leq 1 \text{ ms} \end{array}$ | -   | <b>–15</b>  | Α    |
| I <sub>B</sub>  | base current              |  | -   | -1          | Α    |

 Table 5.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter               | Conditions                  | Min          | Max  | Unit |
|------------------|-------------------------|-----------------------------|--------------|------|------|
| P <sub>tot</sub> | total power dissipation | $T_{amb} \le 25  ^{\circ}C$ | <u>[1]</u> - | 770  | mW   |
|                  |                         |                             | [2] _        | 1700 | mW   |
|                  |                         |                             | [3] _        | 2600 | mW   |
| Tj               | junction temperature    |                             | -            | 150  | °C   |
| T <sub>amb</sub> | ambient temperature     |                             | -55          | +150 | °C   |
| T <sub>stg</sub> | storage temperature     |                             | -65          | +150 | °C   |
|                  |                         |                             |              |      |      |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig 1. Power derating curves

## **Thermal characteristics**

Table 6. **Thermal characteristics** 

| Symbol   | Parameter  | Conditions  | Min          | Тур | Max | Unit |
|--|--|-------------|--------------|-----|-----|------|
| R <sub>th(j-a)</sub> thermal resistance from junction to ambient | thermal resistance from                          | in free air | <u>[1]</u> - | -   | 160 | K/W  |
|  | junction to ambient                              |             | [2] _        | -   | 75  | K/W  |
|  |  |             | <u>[3]</u> _ | -   | 50  | K/W  |
| $R_{th(j-sp)}$   | thermal resistance from junction to solder point |             | -            | -   | 11  | K/W  |

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

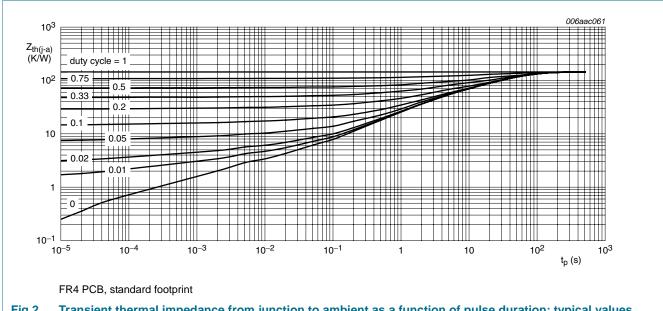


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

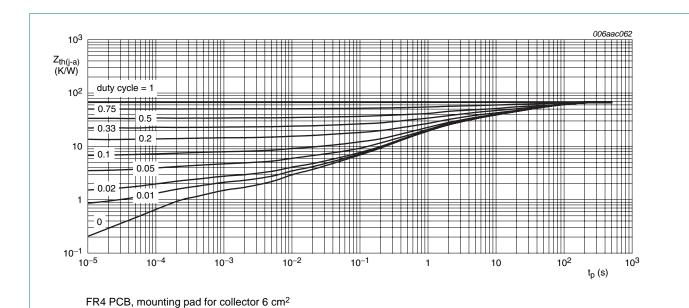
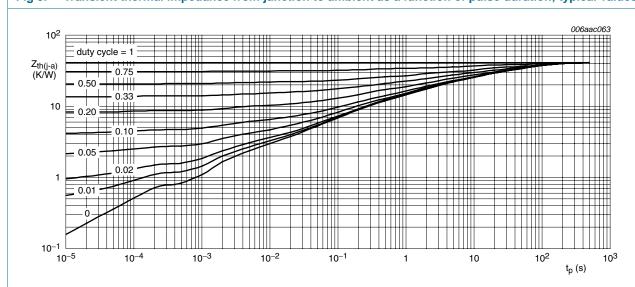


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

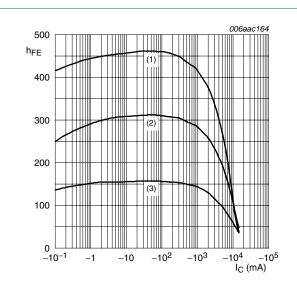
# 7. Characteristics

Table 7. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

| Symbol                               | Parameter                                   | Conditions   |            | Min  | Тур   | Max   | Unit |
|--------------------------------------|---|--|------------|------|-------|-------|------|
| I <sub>CBO</sub>                     |   | $V_{CB} = -60 \text{ V}; I_E = 0 \text{ A}$                                  |            | -    | -     | -100  | nA   |
|                                      | current                                     | $V_{CB} = -60 \text{ V}; I_E = 0 \text{ A};$<br>$T_j = 150 ^{\circ}\text{C}$ |            | -    | -     | -55   | μА   |
| I <sub>CES</sub>                     | collector-emitter<br>cut-off current        | $V_{CE} = -48 \text{ V}; V_{BE} = 0 \text{ V}$                               |            | -    | -     | -100  | nA   |
| I <sub>EBO</sub>                     | emitter-base cut-off current                | $V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$                                   |            | -    | -     | -100  | nA   |
| h <sub>FE</sub>                      | DC current gain                             |  | [1]        |      |       |       |      |
|                                      |   | $V_{CE} = -2 \text{ V};$ $I_{C} = -500 \text{ mA}$                           |            | 200  | 300   | -     |      |
|                                      |   | $V_{CE} = -2 \text{ V}; I_{C} = -1 \text{ A}$                                |            | 200  | 300   | -     |      |
|                                      |   | $V_{CE} = -2 \text{ V}; I_{C} = -2 \text{ A}$                                |            | 200  | 300   | -     |      |
|                                      |   | $V_{CE} = -2 \text{ V}; I_{C} = -4 \text{ A}$                                |            | 150  | 250   | -     |      |
|                                      |   | $V_{CE} = -2 \text{ V}; I_{C} = -6 \text{ A}$                                |            | 120  | 200   | -     |      |
| V <sub>CEsat</sub> collector-emitter |   |  | <u>[1]</u> |      |       |       |      |
|                                      | saturation voltage                          | $I_C = -1 \text{ A}; I_B = -50 \text{ mA}$                                   |            | -    | -42   | -63   | mV   |
|                                      |   | $I_C = -1 \text{ A}; I_B = -10 \text{ mA}$                                   |            | -    | -82   | -125  | mV   |
|                                      |   | $I_C = -2 \text{ A}; I_B = -40 \text{ mA}$                                   |            | -    | -98   | -150  | mV   |
|                                      | $I_C = -4 \text{ A}; I_B = -200 \text{ mA}$ |  | -          | -130 | -195  | mV    |      |
|                                      | $I_C = -4 \text{ A}; I_B = -400 \text{ mA}$ |  | -          | -115 | -175  | mV    |      |
|                                      |   | $I_C = -6 \text{ A}; I_B = -300 \text{ mA}$                                  |            | -    | -190  | -285  | mV   |
| R <sub>CEsat</sub>                   | collector-emitter saturation resistance     | $I_C = -5 \text{ A}; I_B = -500 \text{ mA}$                                  | [1]        | -    | 29    | 43.5  | mΩ   |
| V <sub>BEsat</sub>                   | base-emitter                                | $I_C = -1 A$ ; $I_B = -100 \text{ mA}$                                       | <u>[1]</u> | -    | -0.82 | -0.9  | V    |
|                                      | saturation voltage                          | $I_C = -4 \text{ A}; I_B = -400 \text{ mA}$                                  | [1]        | -    | -0.98 | -1.05 | V    |
| $V_{BEon}$                           | base-emitter turn-on voltage                | $V_{CE} = -2 \text{ V}; I_{C} = -2 \text{ A}$                                | <u>[1]</u> | -    | -0.74 | -0.85 | V    |
| t <sub>d</sub>                       | delay time                                  | $V_{CC} = -12.5 \text{ V};$  |            | -    | 60    | -     | ns   |
| t <sub>r</sub>                       | rise time                                   | $I_C = -1 \text{ A}; I_{Bon} = -0.05 \text{ A};$                             |            | -    | 60    | -     | ns   |
| t <sub>on</sub>                      | turn-on time                                | $I_{Boff} = 0.05 A$  |            | -    | 120   | -     | ns   |
| t <sub>s</sub>                       | storage time                                |  |            | -    | 530   | -     | ns   |
| t <sub>f</sub>                       | fall time                                   |  |            | -    | 100   | -     | ns   |
| t <sub>off</sub>                     | turn-off time                               |  |            | -    | 630   | -     | ns   |
| f <sub>T</sub>                       | transition frequency                        | $V_{CE} = -10 \text{ V};$ $I_{C} = -100 \text{ mA};$ $f = 100 \text{ MHz}$   |            | -    | 110   | -     | MHz  |
| C <sub>c</sub>                       | collector capacitance                       | $V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A}; f = 1 \text{ MHz}$       |            | -    | 85    | -     | pF   |

<sup>[1]</sup> Pulse test:  $t_p \leq 300~\mu s;~\delta \leq 0.02.$ 



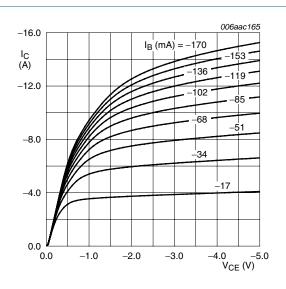
$$V_{CE} = -2 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

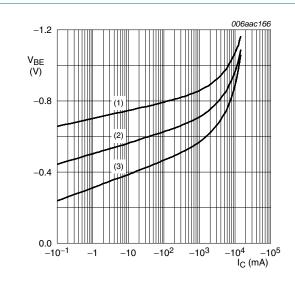
(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 5. DC current gain as a function of collector current; typical values



T<sub>amb</sub> = 25 °C

Fig 6. Collector current as a function of collector-emitter voltage; typical values



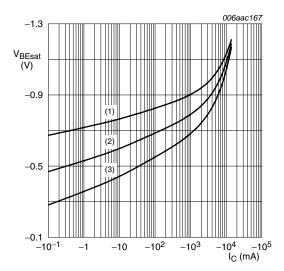
$$V_{CE} = -2 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig 7. Base-emitter voltage as a function of collector current; typical values



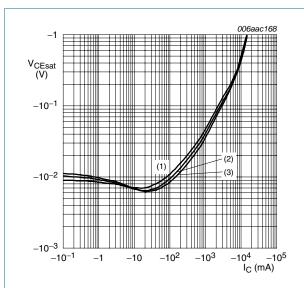
 $I_{\rm C}/I_{\rm B} = 20$ 

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig 8. Base-emitter saturation voltage as a function of collector current; typical values



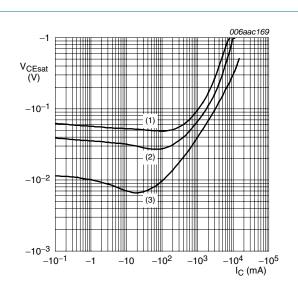
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



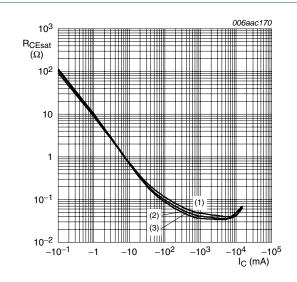
$$T_{amb} = 25 \, ^{\circ}C$$

(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values



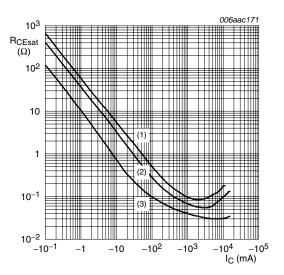
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values



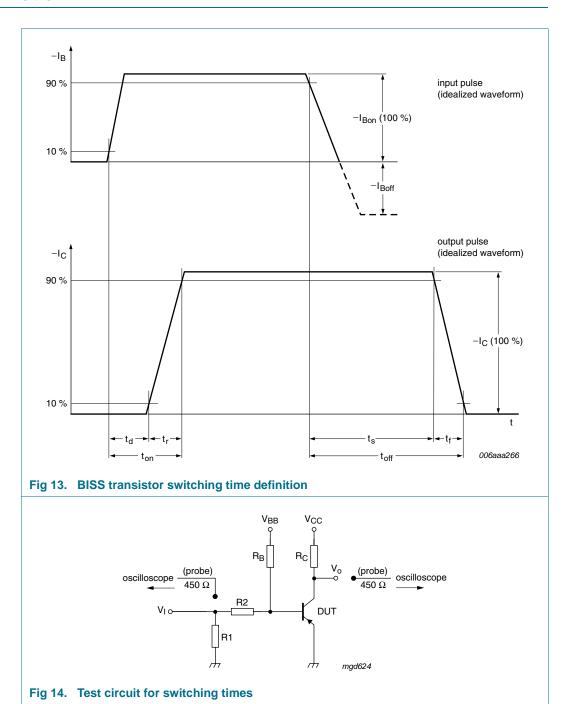
(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values

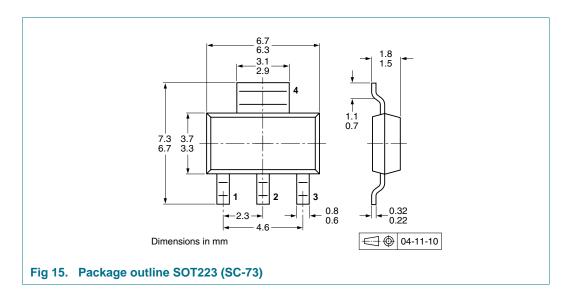
## 8. Test information



## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 9. Package outline



# 10. Packing information

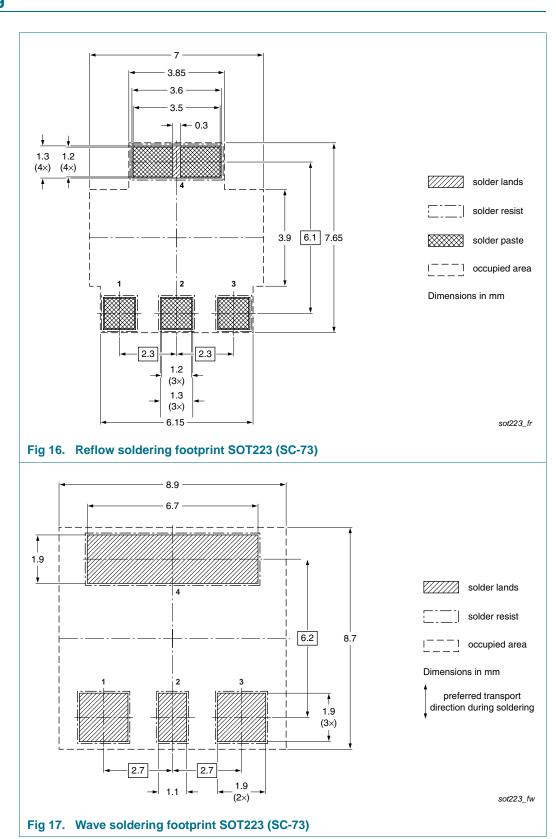
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

| Type number | Package | Description                     | Packing o | uantity |
|-------------|---------|---------------------------------|-----------|---------|
|             |         |                                 | 1000      | 4000    |
| PBSS4041PZ  | SOT223  | 8 mm pitch, 12 mm tape and reel | -115      | -135    |

<sup>[1]</sup> For further information and the availability of packing methods, see Section 14.

# 11. Soldering



Nexperia PBSS4041PZ

60 V, 5.7 A PNP low V<sub>CEsat</sub> (BISS) transistor

# 12. Revision history

## Table 9. Revision history

| Document ID  | Release date | Data sheet status  | Change notice | Supersedes |
|--------------|--------------|--------------------|---------------|------------|
| PBSS4041PZ_1 | 20100331     | Product data sheet | -             | -          |

## 13. Legal information

#### 13.1 Data sheet status

| Document status[1][2]          | Product status[3] | Definition  |
|--------------------------------|-------------------|---|
| Objective [short] data sheet   | Development       | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification     | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production        | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PBSS4041P7 1

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Nexperia PBSS4041PZ

60 V, 5.7 A PNP low V<sub>CEsat</sub> (BISS) transistor

## 14. Contact information

For more information, please visit: <a href="http://www.nexperia.com">http://www.nexperia.com</a>

For sales office addresses, please send an email to:  $\underline{\textbf{salesaddresses@nexperia.com}}$ 

PBSS4041PZ

## **Nexperia**

60 V, 5.7 A PNP low V<sub>CEsat</sub> (BISS) transistor

## 15. Contents

| 1    | Product profile         |
|------|-------------------------|
| 1.1  | General description     |
| 1.2  | Features and benefits   |
| 1.3  | Applications            |
| 1.4  | Quick reference data 1  |
| 2    | Pinning information     |
| 3    | Ordering information    |
| 4    | Marking                 |
| 5    | Limiting values         |
| 6    | Thermal characteristics |
| 7    | Characteristics         |
| 8    | Test information 9      |
| 8.1  | Quality information     |
| 9    | Package outline         |
| 10   | Packing information     |
| 11   | Soldering 11            |
| 12   | Revision history        |
| 13   | Legal information       |
| 13.1 | Data sheet status       |
| 13.2 | Definitions             |
| 13.3 | Disclaimers             |
| 13.4 | Trademarks13            |
| 14   | Contact information 14  |
| 15   | Contents                |